

AMENDMENTS TO THE CLAIMS

The listing of claims below replaces all prior versions of claims in the application.

1. (Currently Amended): A semiconductor device fabrication method comprising:

a first polishing of ~~polishing a surface of~~ a film-to-be-polished while a polishing slurry including abrasive grains and a surfactant is supplied onto a polishing pad through a first nozzle; and

a second polishing of ~~polishing the surface of~~ the film-to-be-polished while said polishing slurry is supplied onto a polishing pad through the first nozzle and water is further supplied onto the polishing pad through a second nozzle different from the first nozzle,

wherein supply of said water through the second nozzle starts at the second polishing after the first polishing.

2. (Cancelled)

3. (Previously Presented): A semiconductor device fabrication method according to claim 1, wherein

in the second polishing, said water is supplied to a first position on a polishing table, and the polishing slurry is supplied to a second position on the polishing table,

wherein a distance between the first position and a center position of the polishing table is larger than a distance between the center position and the second position.

4. (Previously Presented): A semiconductor device fabrication method according to claim 1, wherein

in the second polishing, a supply amount of said water is 2 or more times as much as a supply amount of said polishing slurry.

5.-11. (Cancelled)

12. (Currently Amended): A semiconductor device fabrication method according to claim 1, further comprising, before the first polishing:

forming over a semiconductor substrate an insulation film having polish characteristics different from those of the film-to-be-polished;

forming an opening in the insulation film;

etching the semiconductor substrate with the insulation film as a mask to form a trench in the semiconductor substrate; and

forming the film-to-be-polished in the trench and over the insulation film,
in the second polishing, ~~the surface of~~ the film-to-be-polished is polished with the
insulation film as a stopper.

13.-27. (Cancelled)

28. (Previously Presented): A semiconductor device fabrication method according to
claim 1, wherein

the abrasive grains comprise cerium oxide or silicon oxide,
the surfactant comprises poly(ammonium acrylate).

29.-33. (Cancelled)

34. (Previously Presented): A semiconductor device fabrication method according to
claim 1, wherein

in the second polishing, a supply amount of said polishing slurry to a supply amount of
said water is 1:5.

35. (Previously Presented): A semiconductor device fabrication method according to
claim 1, wherein the polishing pad used in the second polishing is different from the polishing
pad used in the first polishing.

Amendment under 37 C.F.R. §1.312
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36. (Cancelled)